



YJG40GP06A

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-60V
I_D	-40A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	25 mohm
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	30 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
Low $R_{DS(on)}$ & FOM
Low C_{rss}
Extremely low switching loss
Excellent stability and uniformity
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Load Switch
Industrial DC/DC Conversion Circuits

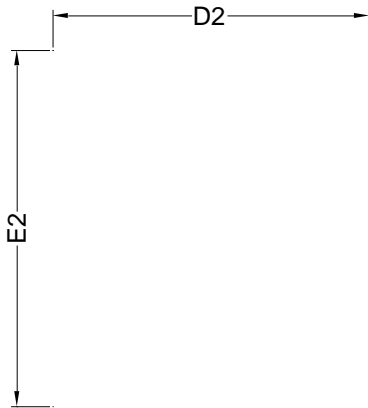
Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}		



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PDFN5060-8L-B-1.1MM



Top View

Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1			

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



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